PSMN3R3-80BS

N-channel 80 V, 3.5 mΩ standard level MOSFET in D2PAK

Rev. 2 — 29 February 2012 **Product data sheet**

1. Product profile

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switch
- Motor control
- Server power supplies

1.4 Quick reference data

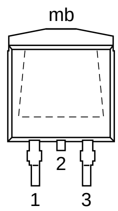
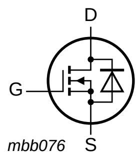
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	80	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1 [1]	-	-	120	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	-	306	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 13	-	3	3.5	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12; see Figure 13	-	4.95	5.8	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 75 A; V_{DS} = 40 V; see Figure 14; see Figure 15	-	28	-	nC
$Q_{G(tot)}$	total gate charge		-	111	-	nC
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \leq 80$ V; R_{GS} = 50 Ω; unclamped	-	-	676	mJ

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SOT404 (D2PAK)	
2	D	drain		
3	S	source		
mb	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R3-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

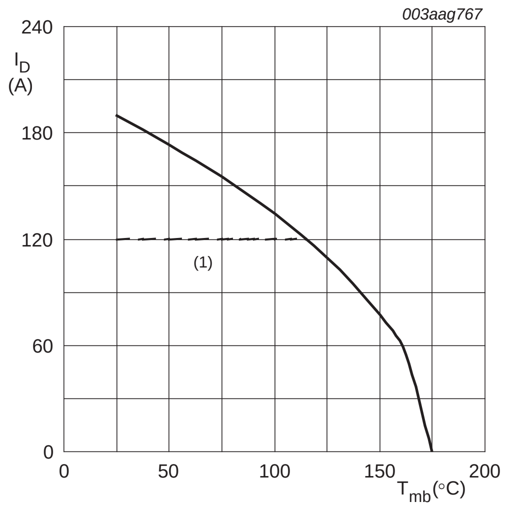
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

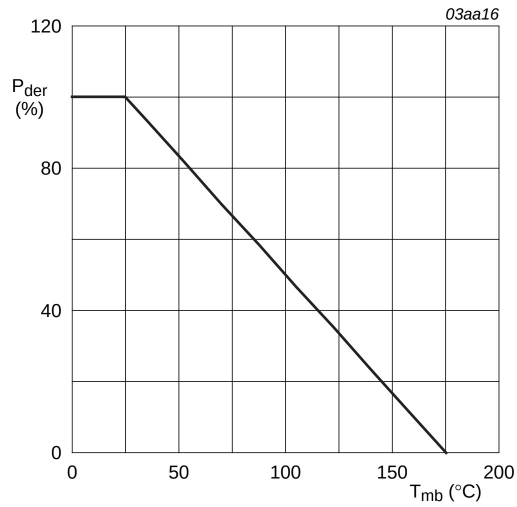
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	80	V
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C; $R_{GS} = 20$ kΩ		-	80	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_{mb} = 100$ °C; see Figure 1	[1]	-	120	A
		$V_{GS} = 10$ V; $T_{mb} = 25$ °C; see Figure 1	[1]	-	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C; see Figure 3		-	760	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2		-	306	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25$ °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C		-	760	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 120$ A; $V_{sup} \leq 80$ V; $R_{GS} = 50$ Ω; unclamped		-	676	mJ

[1] Continuous current is limited by package.



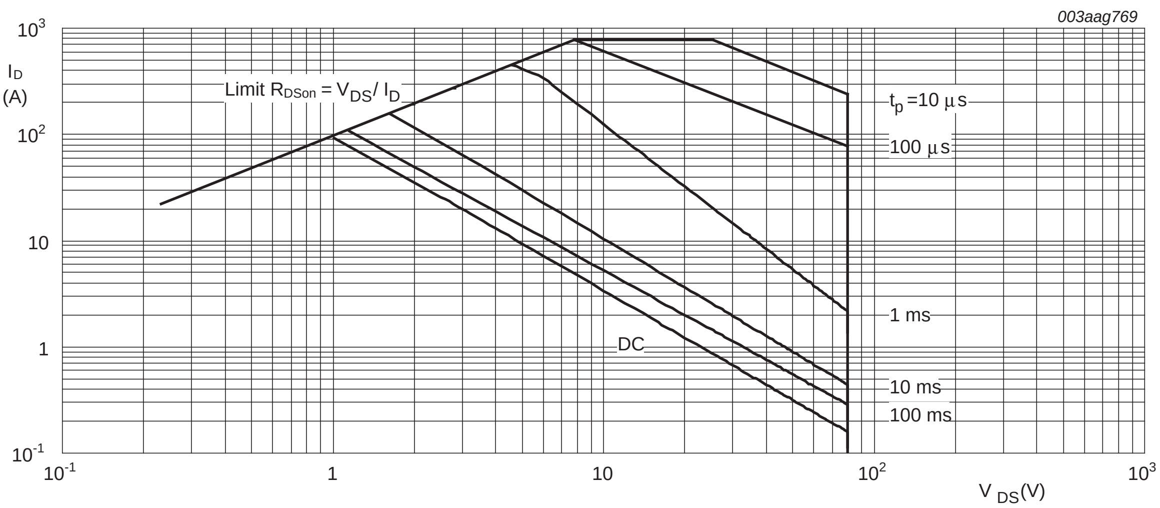
$V_{GS} \geq 10$ V; (1) Capped at 120 A due to package

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed circuit board	-	50	-	K/W

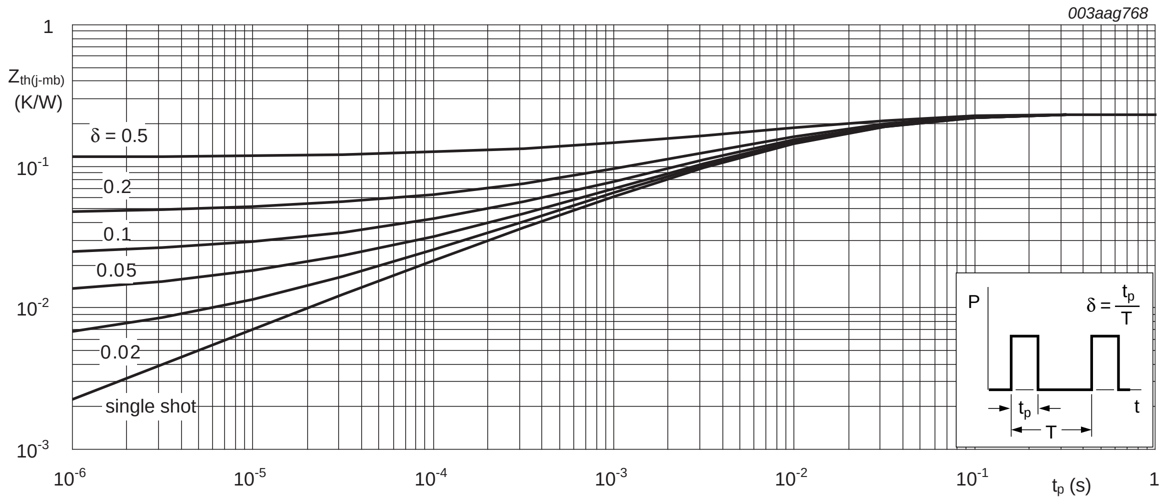


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	73	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 10	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 10	-	-	4.6	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 10;see Figure 11	2	3	4	V
I_{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	10	µA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 12;see Figure 13	-	7.1	8.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 13	-	3	3.5	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12;see Figure 13	-	4.95	5.8	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V	-	104	-	nC
		I_D = 75 A; V_{DS} = 40 V; V_{GS} = 10 V; see Figure 14; see Figure 15	-	111	-	nC
Q_{GS}	gate-source charge		-	38	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	24	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	14	-	nC
Q_{GD}	gate-drain charge		-	28	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 75 A; V_{DS} = 40 V; see Figure 14; see Figure 15	-	6.1	-	V
C_{iss}	input capacitance	V_{DS} = 40 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 16	-	8161	-	pF
C_{oss}	output capacitance		-	701	-	pF
C_{rss}	reverse transfer capacitance		-	337	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 40 V; R_L = 0.53 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 4.7 Ω; I_D = 75 A	-	38	-	ns
t_r	rise time		-	29	-	ns
$t_{d(off)}$	turn-off delay time		-	94	-	ns
t_f	fall time		-	33	-	ns

Table 6. Characteristics *...continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 17	-	0.8	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = 100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V	-	59	-	ns
Q_r	recovered charge		-	109	-	nC

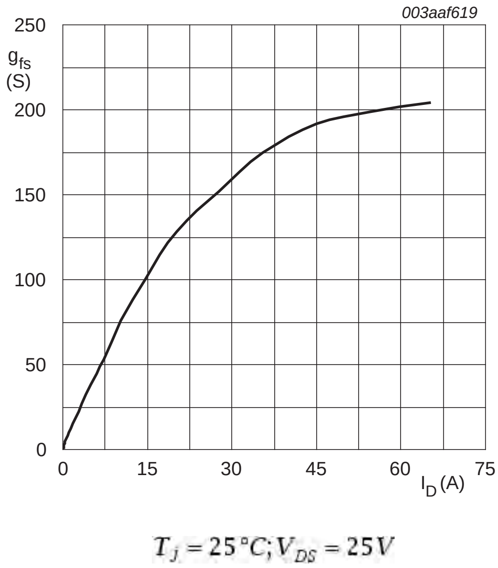


Fig 5. Forward transconductance as a function of drain current; typical values

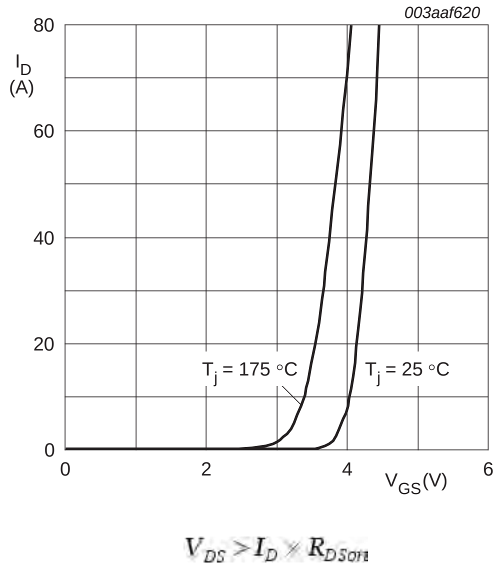


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

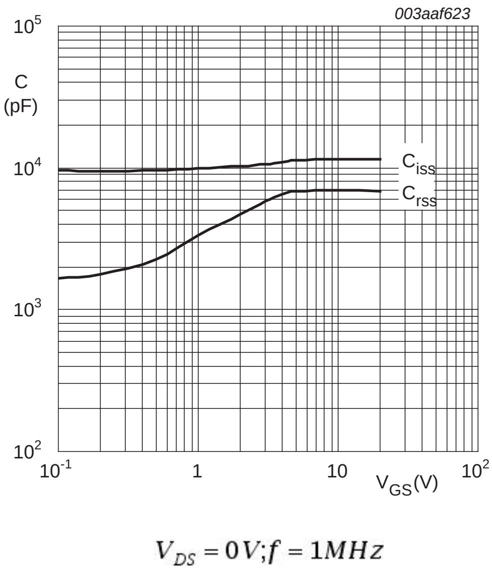


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

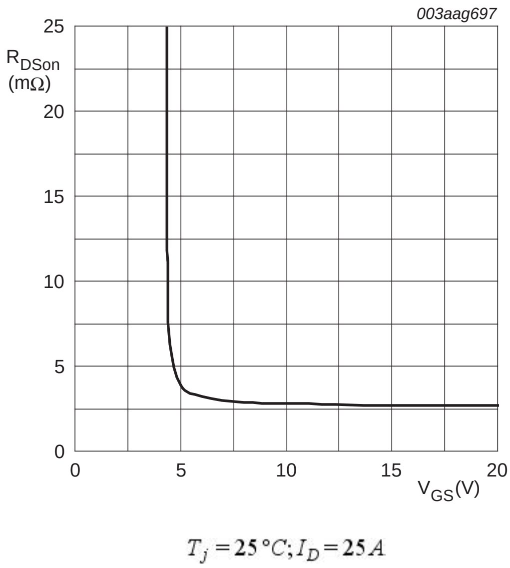
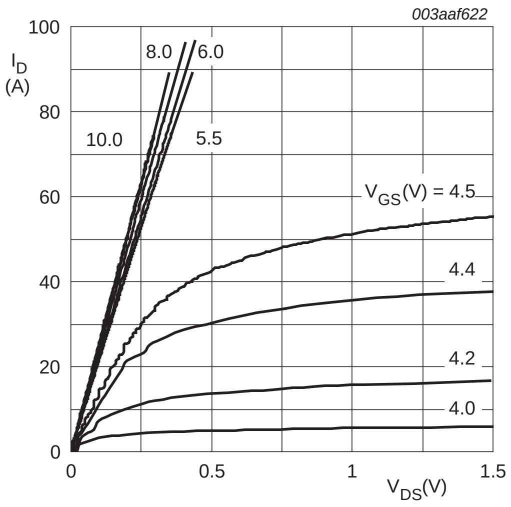
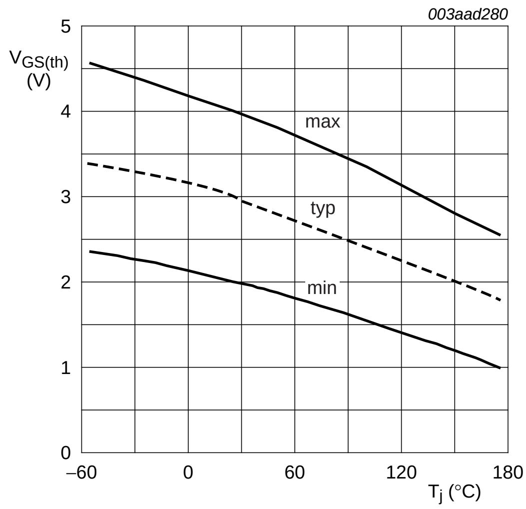


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



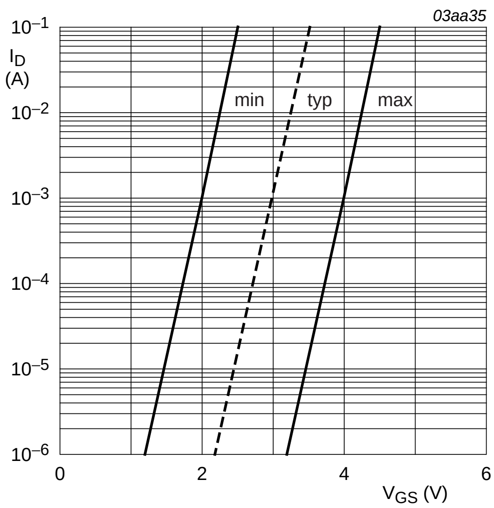
$T_j = 25\,°C$

Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values



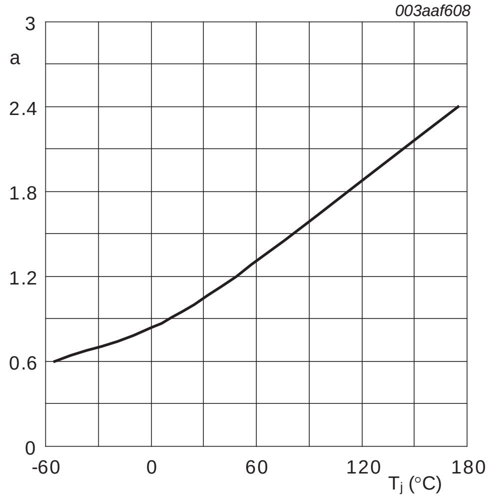
$I_D = 1\,\text{mA};\ V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



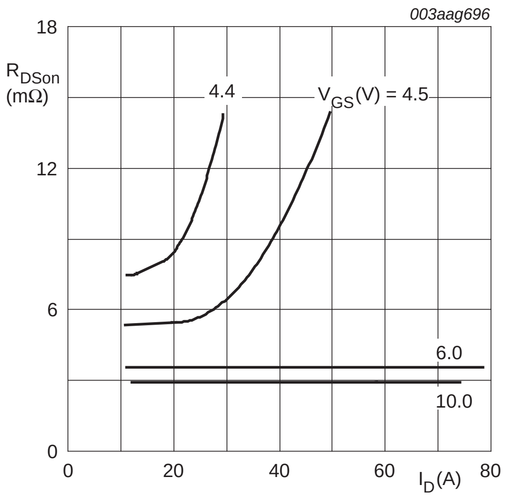
$T_j = 25\,°C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 12. Normailzed drain-source on-state resistance factor as a function of junction temperature



$T_j = 25\,°C; I_D = 25\,A$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

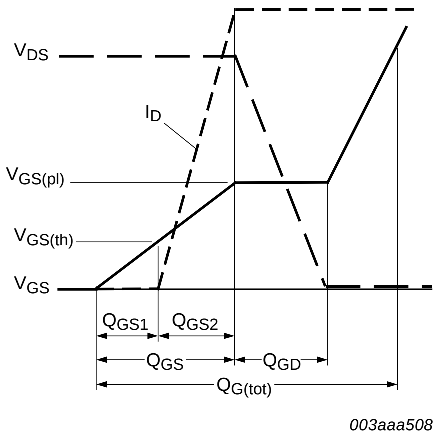
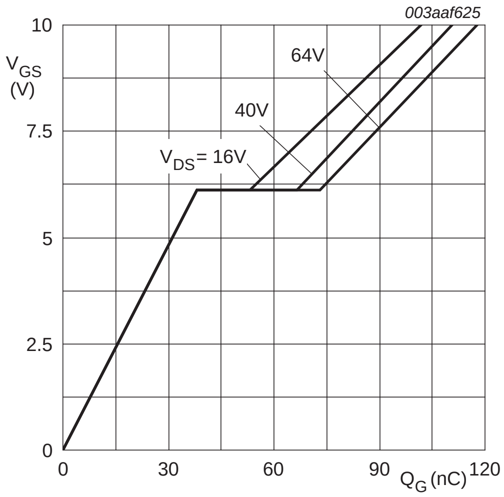
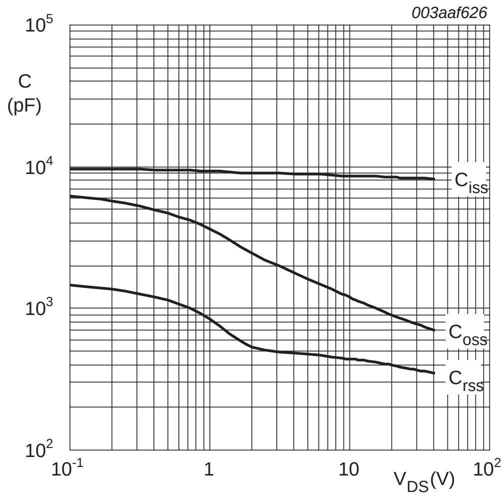


Fig 14. Gate charge waveform definitions



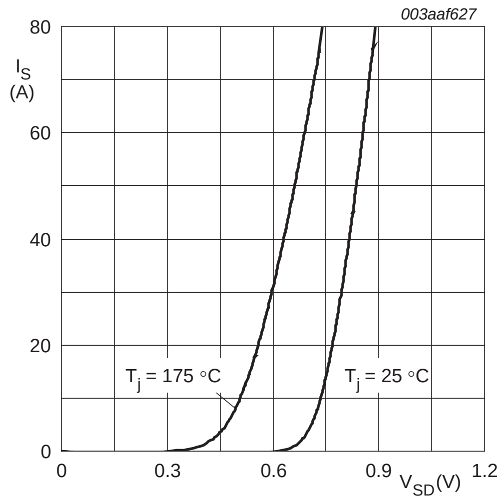
$I_D = 75\,A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\,V; f = 1\,MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

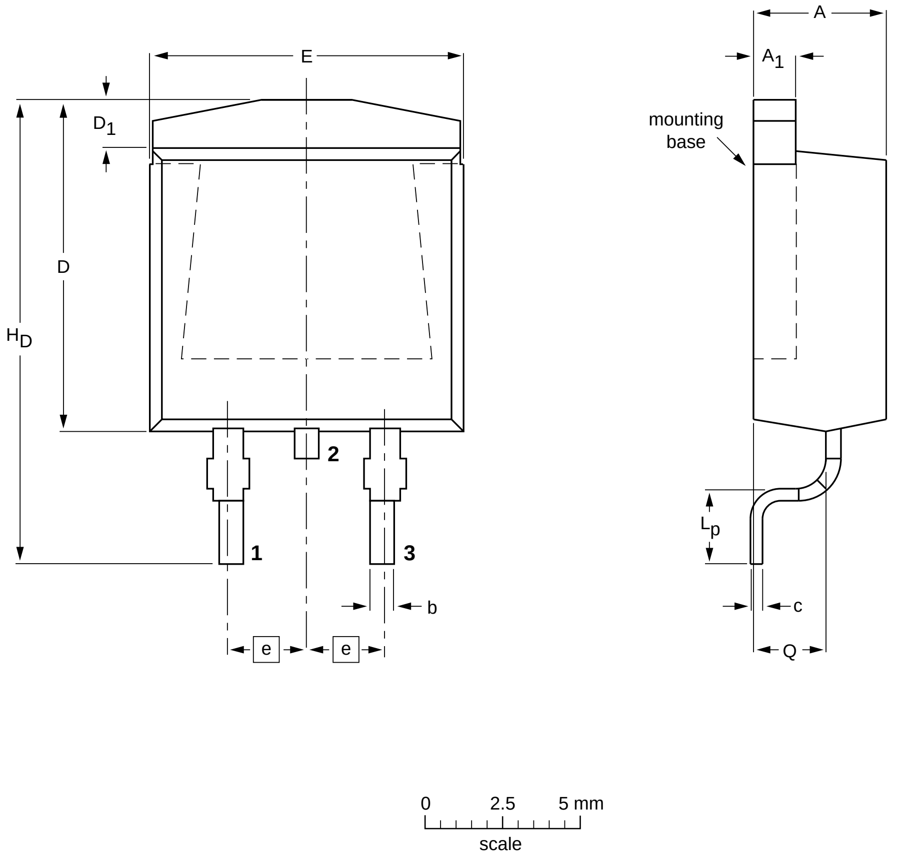


$V_{GS} = 0\,V$

Fig 17. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						~~05-02-11~~ 06-03-16

Fig 18. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R3-80BS v.2	20120229	Product data sheet	-	PSMN3R3-80BS v.1
Modifications:	• Status changed from objective to product. • Various changes to content.			
PSMN3R3-80BS v.1	20110928	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URLhttp://www.nxp.com.

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11. Contents

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